SSO Noise And Conducted EMI: Modeling, Analysis, And Design Solutions

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Today's I/Os Challenges 2

- Higher I/O count
- Increasing operating frequencies
- Faster signal edge rates
- High I/O density makes it difficult to place PCB decaps close enough to the pads
- Automotive specific challenge: I/Os signal conducted EMI
- EMC and signal integrity are another mandatory objective for first silicon success



EMC At The End Of The Design Flow





Our Vision: EMC-Aware Design





Reflection, Crosstalk, And SSO Noise



SSO Noise And Conducted EMI





System-Level EMI Simulation Flow



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I/O Ring Circuit

- Any realistic signal integrity and EMI simulation must include the complete system-level macromodel (die, package, board)
- A full transistor-level simulation of the I/O ring is impractical even for a limited number of adjacent toggling I/Os and a given victim





SSO Flow





I/O Bank For EMI Analysis





Design Solutions For SSO Noise Reduction _____

- I/Os' signal skewing
- I/O ring fillercap insertion
- I/O pads reduced driving strength
- I/O ring power/ground supply placement



I/O Skewing Impact on EMI 12

- Typical I/Os' working frequency for automotive applications are in the range of a few KHz and do not need to toggle synchronously
 - A relative skew in the range of about 10ns is compatible with a correct functionality of the I/O ring
- Harmonic amplitude reduction of several dBµVs obtained in the frequency range of 1GHz





I/O Fillercaps Insertion And Driving Strength Reduction

- I/O fillercap insertion did not prove to be an effective technique
 - Huge amount of decaps and related area to achieve only few $dB\mu V$ amplitude reduction
 - Difficult to exploit this technique on typical pad-limited I/O rings
- I/O driving strength reduction (when compliant with the timing constraints) from MEDIUM to SLOW strength version can further reduce the SSO noise





SSO Flow Validation 14

• The gate-level SSO flow was validated vs. full Spice-level simulations



SSO Flow Validation 15

The gate-level SSO flow was validated vs. full Spice-level simulations





IBIS For SSO And EMI Analysis

- Traditionally IBIS models have been used for signal integrity simulations on system PCBs
 - Behavioral modeling
 - IP protection
 - Fast simulation time
 - Reasonable accuracy
- However IBIS v4.0 cannot include predriver and crossbar currents and I/O ring power/ground supply bouncing which is the dominant source of SSO and conducted EMI
- To validate IBIS v5.0 for EMI analysis the same STYY I/O bank was used
- IBIS v5.0 was compared vs. full transistor-level simulations



IBIS Validation Flow 17



IBIS For SSO And EMI Analysis 18

IBIS v5.0 vs. Spice



Time-domain analysis

Frequency-domain analysis

IBIS vs. Spice: good accuracy up to 2GHz





- CAD flow and design solutions for SSO and I/O conducted EMI analysis and optimization were presented
- Methodology exploited on an industrial automotive microcontroller in ST 90nm with eNVM technology
- IBIS v5.0 can be used for a reliable SSO and EMI analysis

